NEC 304

STLD

Lecture 30

Random Access Memory (RAM)

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Overview

- **Memory is a collection of storage cells with associated input and output circuitry**
  - **Possible to read and write cells**
- **Random access memory (RAM) contains words of information**
- **Data accessed using a sequence of signals**
  - **Leads to timing waveforms**
- **Decoders are an important part of memories**
  - **Selects specific data in the RAM**
- **Static RAM loses values when circuit power is removed.**

Preliminaries

- **RAMs contain a collection of data bytes**
  - **A collection of bytes is called a word**
  - **A sixteen bit word contains two bytes**
  - **Capacity of RAM device is usually described in bytes (e.g. 16 MB)**
- **Write operations write data to specific words**
- **Read operations read data from specific words**
- **Note: new notation for OR gate**

(a) Conventional symbol (b) Array logic symbol

Fig. 7-1 Conventional and Array Logic Diagrams for OR Gate

RAM Interface Signals

- Data input and output lines carry data
- Memory contains 2^k words
  - k address lines select one word out of 2^k
- Read *asserted* when data to be transferred to output
- Write *asserted* when data input to be stored

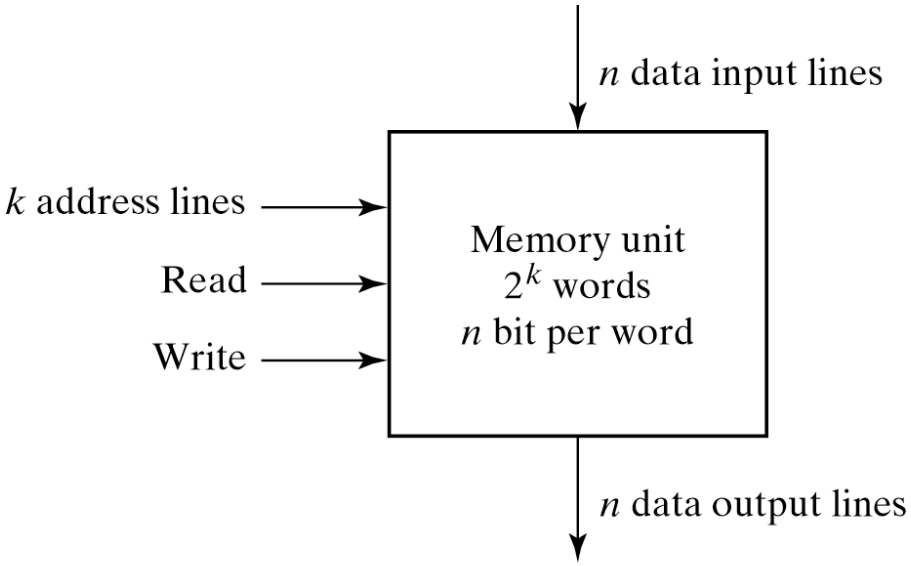


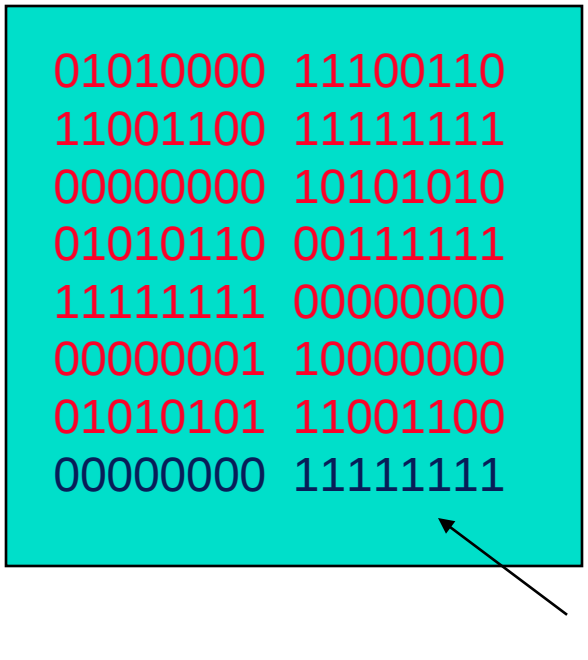
Fig. 7-2 Block Diagram of a Memory Unit

Random Access Memory Fundamentals

- **Lets consider a simple RAM chip**
  - **8 words of 2 bytes each (each word is 16 bits)**
  - **How many address bits do we need?**

Pick one of 8 locations

Dec	Binary
0	000
1	001
2	010
3	011
4	100
5	101
6	110
7	111



16 Data and Input signals

____ address signals

Each bit stored in a binary cell

RAM Size

- If memory has 2^k words, k address bits are needed
  - 2^3 words, 3 address bits
- Address locations are labelled 0 to 2^k-1
- Common subscripts:
  - Kilo – 2^{10}
  - Mega – 2^{20}
  - Giga - 2^{30}

Memory address		Memory contest
Binary	decimal	
0000000000	0	1011010101011101
0000000001	1	1010101110001001
0000000010	2	0000110101000110
⋮	⋮	⋮
1111111101	1021	1001110100010100
1111111110	1022	0000110100011110
1111111111	1023	1101111000100101

Fig. 7-3 Content of a 1024 × 16 Memory

Write Operation

1. **Apply binary address of word to address lines**
2. **Apply data bits to data input lines**
3. **Activate write input**

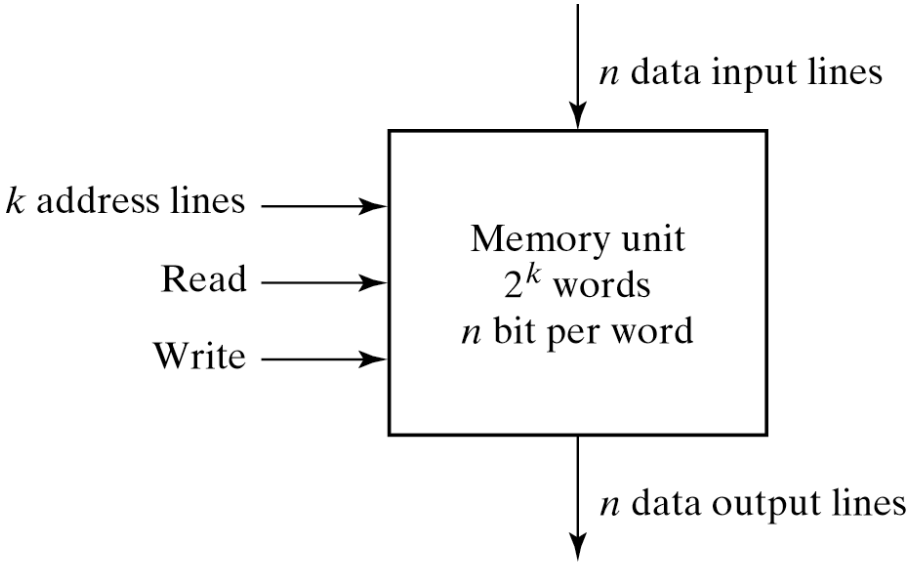


Fig. 7-2 Block Diagram of a Memory Unit

Data output lines unused

Read input signal should be inactive

Delay associated with write

Read Operation

1. **Apply binary address of word to address lines**
2. **Activate read input**

Data input lines unused
Write input signal should be inactive

Delay associated with read

Memory enable used to allow read and writes

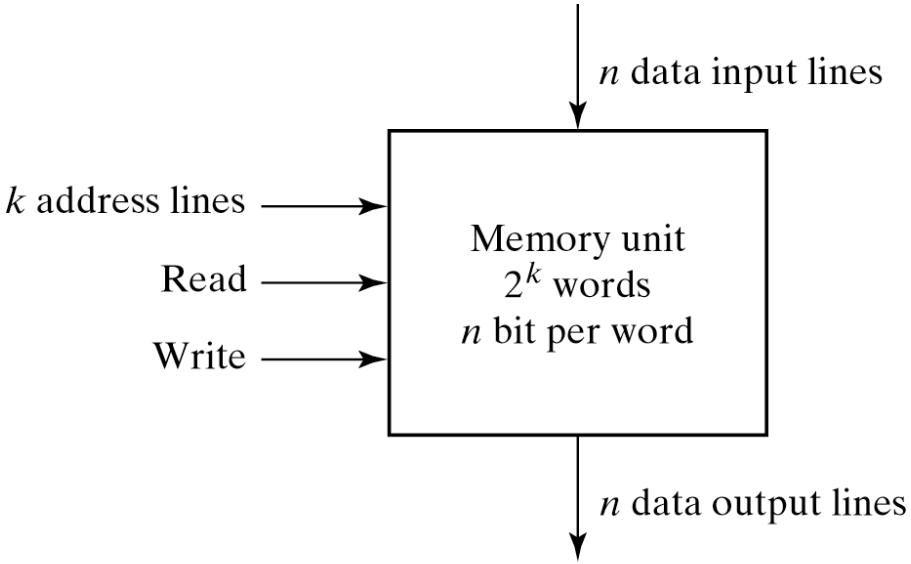
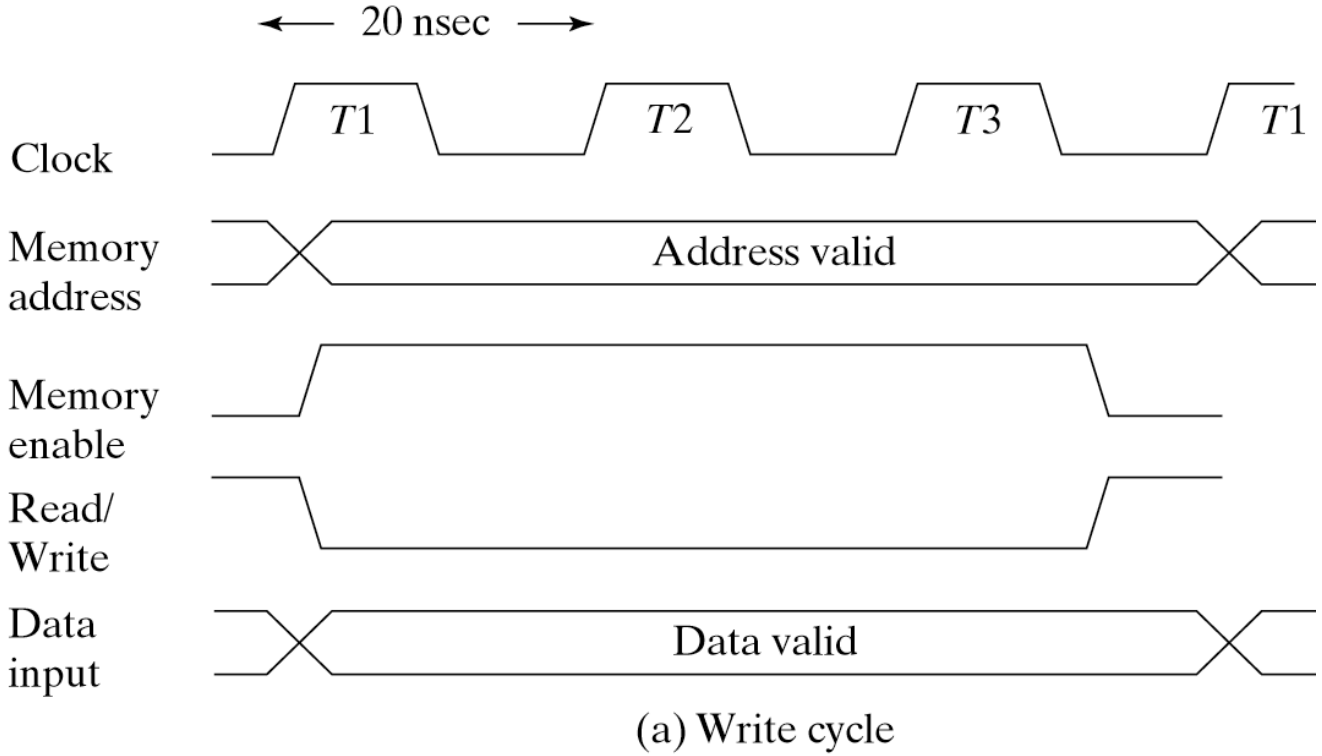


Fig. 7-2 Block Diagram of a Memory Unit

Memory Timing – write operation

- Memory **does not** use a clock
  - Control signals may be generated on clock edges
- Cycle time – time needed to write to memory
- If cycle time is 50 ns, **3** clock edges required **(T1, T2, T3)**



(a) Write cycle

Timing Waveforms – read operation

- **Access time** indicates time to read
- **Address** indicates location
- **Data valid on Data Output following access time**

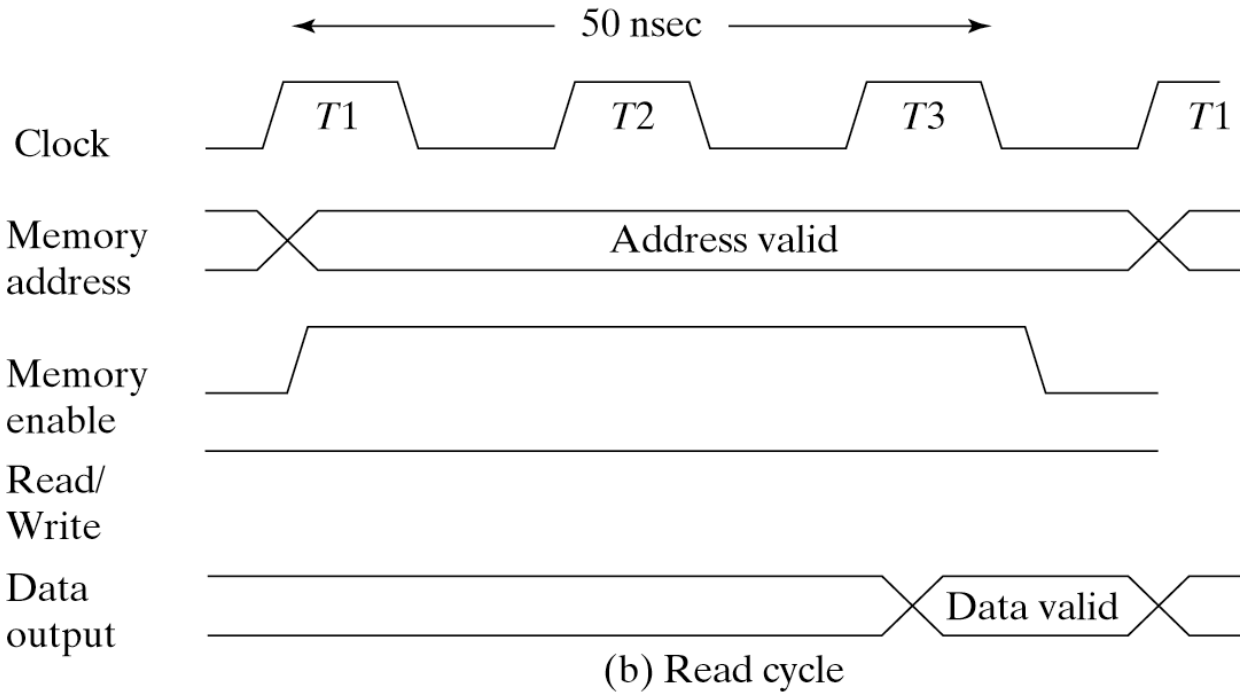


Fig. 7-4 Memory Cycle Timing Waveforms

Multiple clock signals needed for data read in this example

* Note ordering of signals (address, mem enable)

Comments about Memory Access and Timing

- **Most computers have a central processing unit (CPU)**
  - Processor generates control signals, address, and data
  - Values stored and then read from RAM

- **The timing of the system is very important.**
  - Processor provides data for the cycle time on writes
  - Processor waits for the access time for reads

Types of Random Access Memories

- **Static random access memory (SRAM)**
  - Operates like a collection of latches
  - Once value is written, it is guaranteed to remain in the memory as long as power is applied
  - Generally expensive
  - Used inside processors (like the Pentium)
- **Dynamic random access memory (DRAM)**
  - Generally, simpler internal design than SRAM
  - Requires data to be rewritten (refreshed), otherwise data is lost
  - Often hold larger amount of data than SRAM
  - Longer access times than SRAM
  - Used as main memory in computer systems

Inside the RAM Device

- Address inputs go into decoder
  - Only one output active
- Word line selects a row of bits (word)
- Data passes through OR gate
- Each binary cell (BC) stores one bit
- Input data stored if Read/Write is 0
- Output data driven if Read/Write is 1

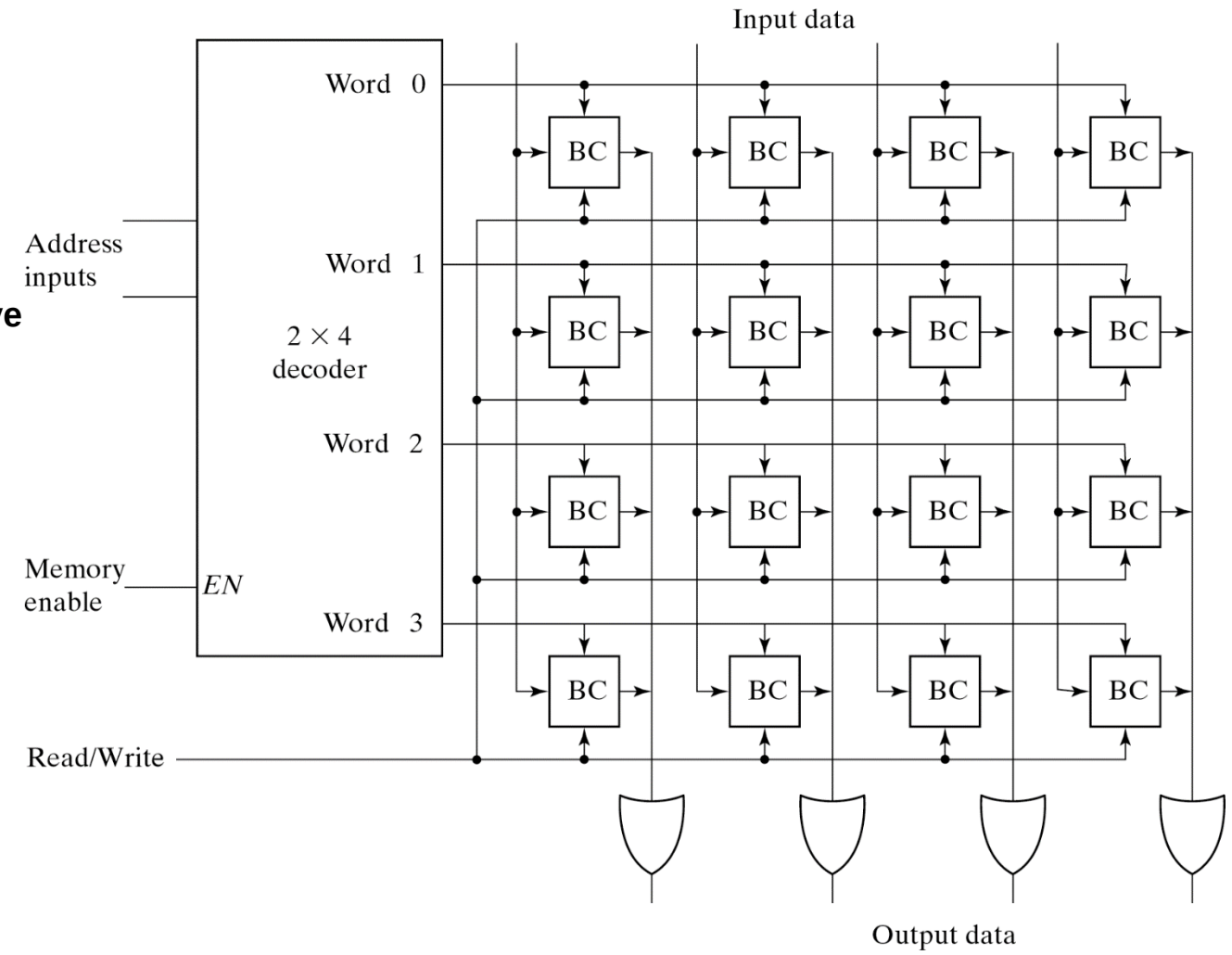
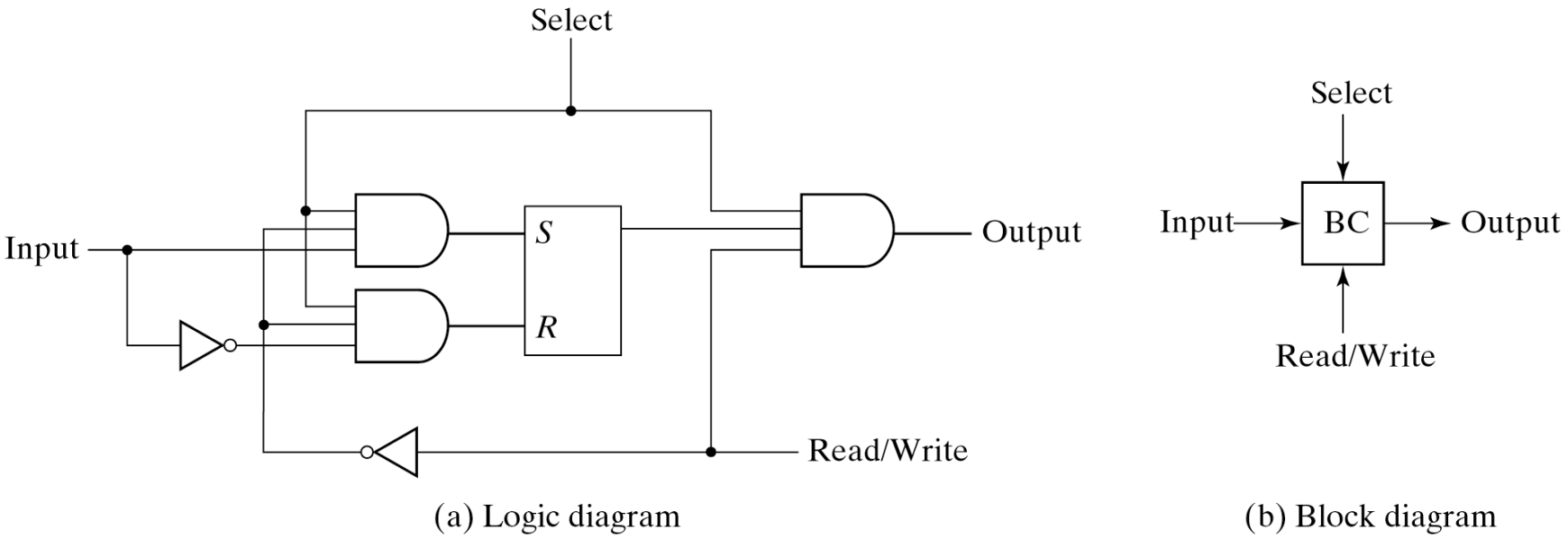


Fig. 7-6 Diagram of a 4 × 4 RAM

Inside the SRAM Device

- Basis of each SRAM cell is an S-R latch
- Note that data goes to both S and R
- Select enables operation
- Read/write enables read or write, but not both



(a) Logic diagram (b) Block diagram

Fig. 7-5 Memory Cell

Inside the SRAM Device

- **Note: delay primarily depends on the number of words**
- **Delay not effected by size of words**

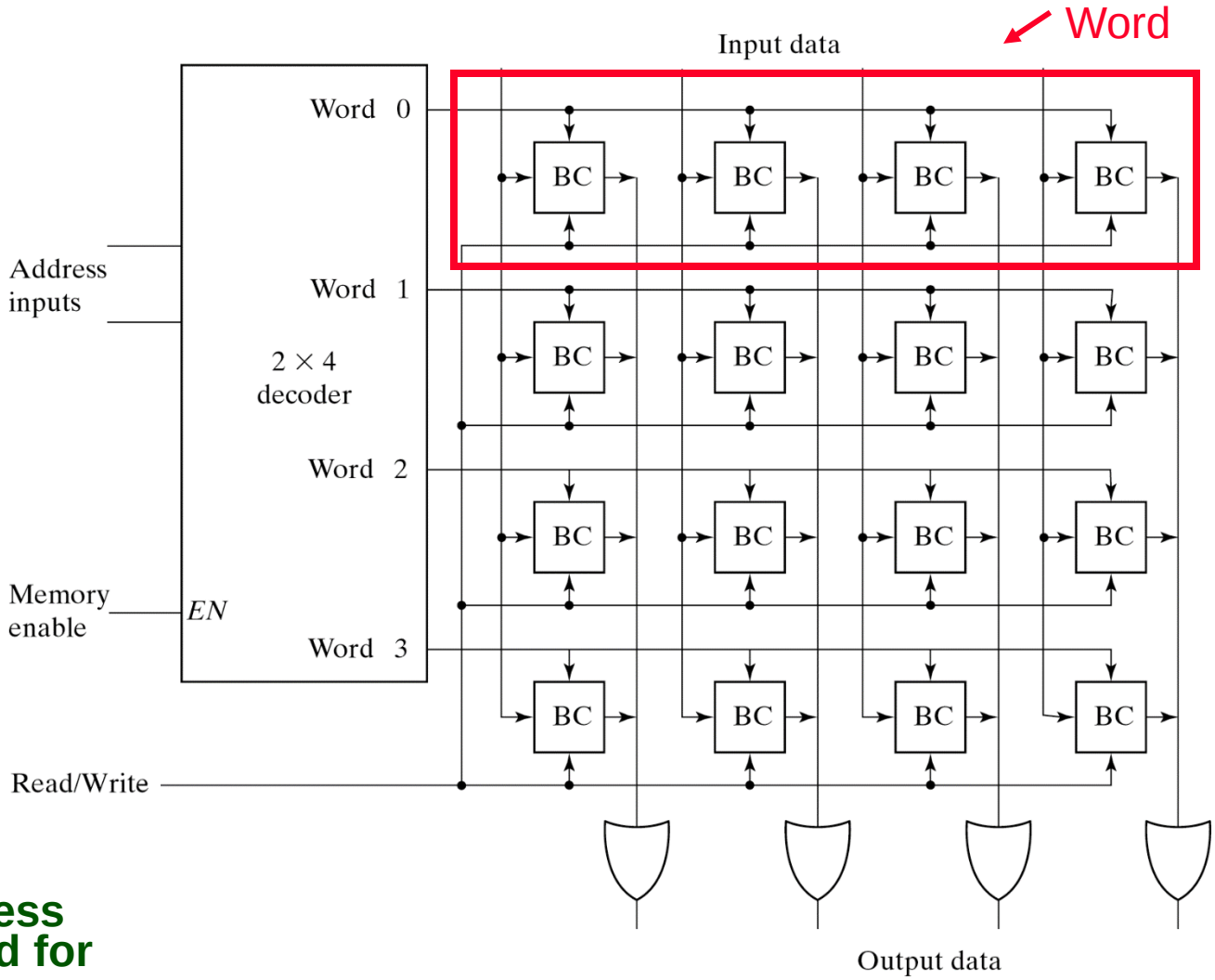


Fig. 7-6 Diagram of a 4 × 4 RAM

- **How many address bits would I need for 16 words?**

Summary

- Memories provide storage for computers
- Memories are organized in words
  - Selected by addresses
- SRAMs store data in latches
  - Accessed by surrounding circuitry
- RAM waveforms indicate the control signals needed for access
- Words in SRAMs are accessed with decoders
  - Only one word selected at a time